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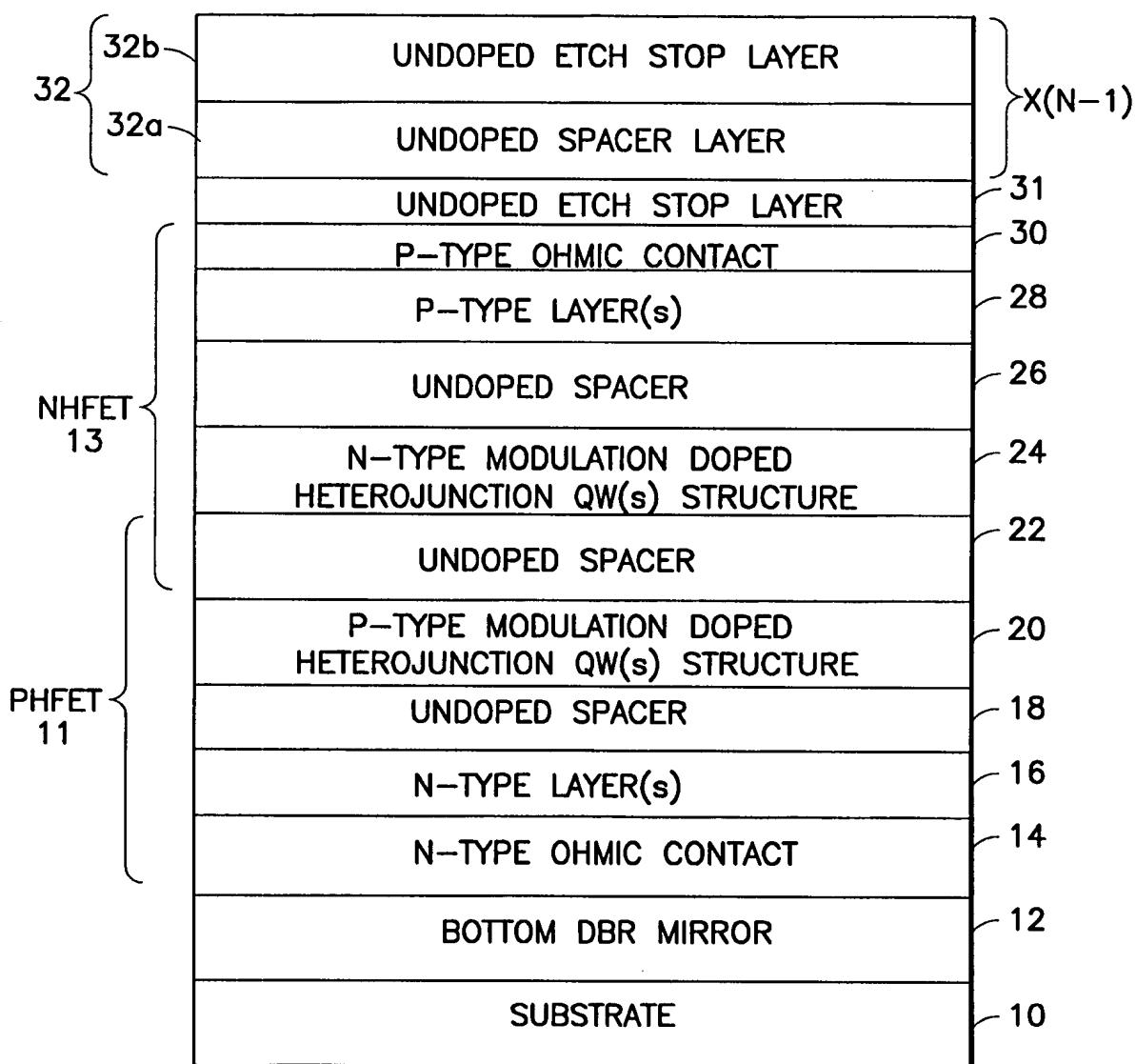


FIG.1

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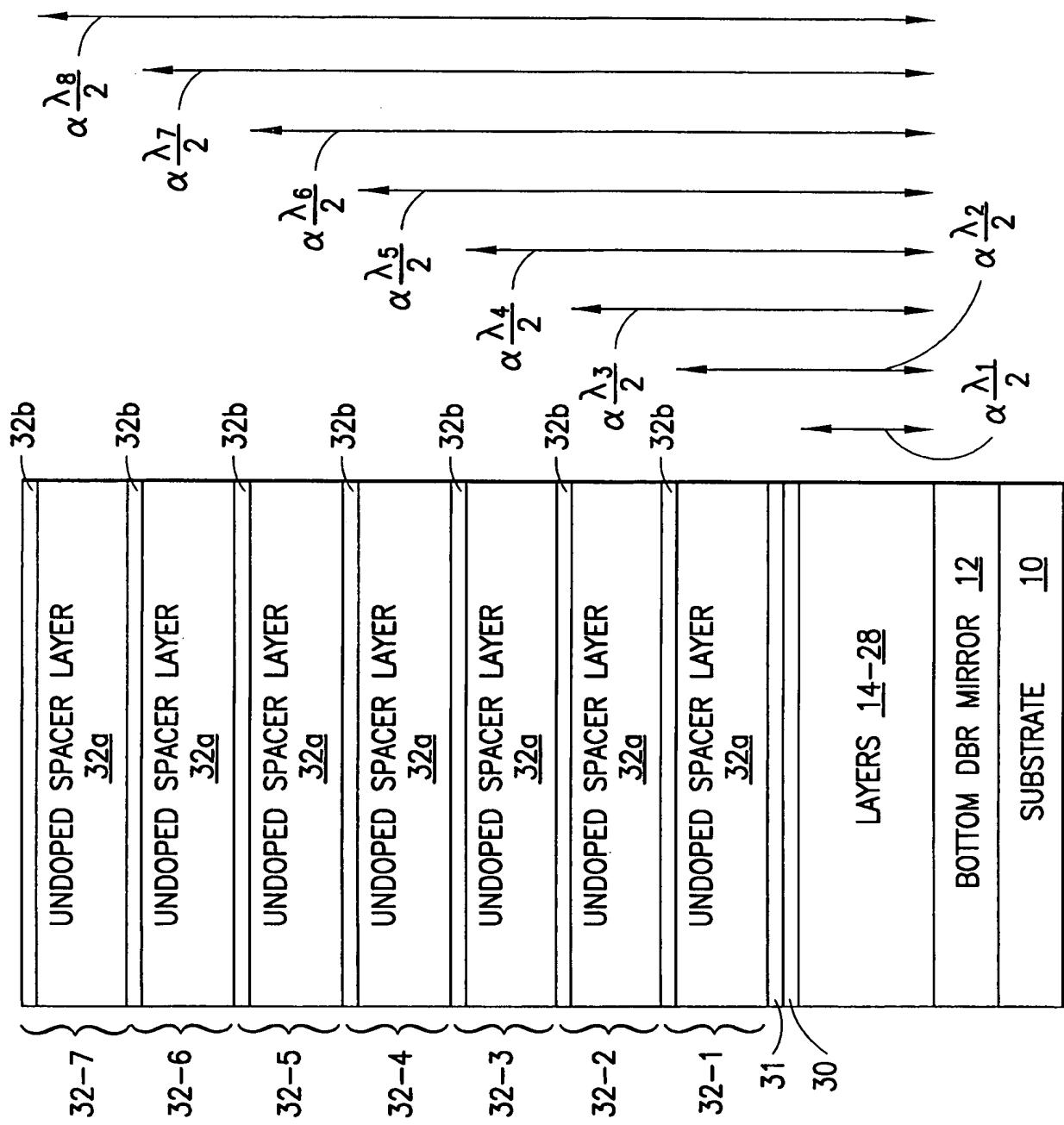


FIG.2A

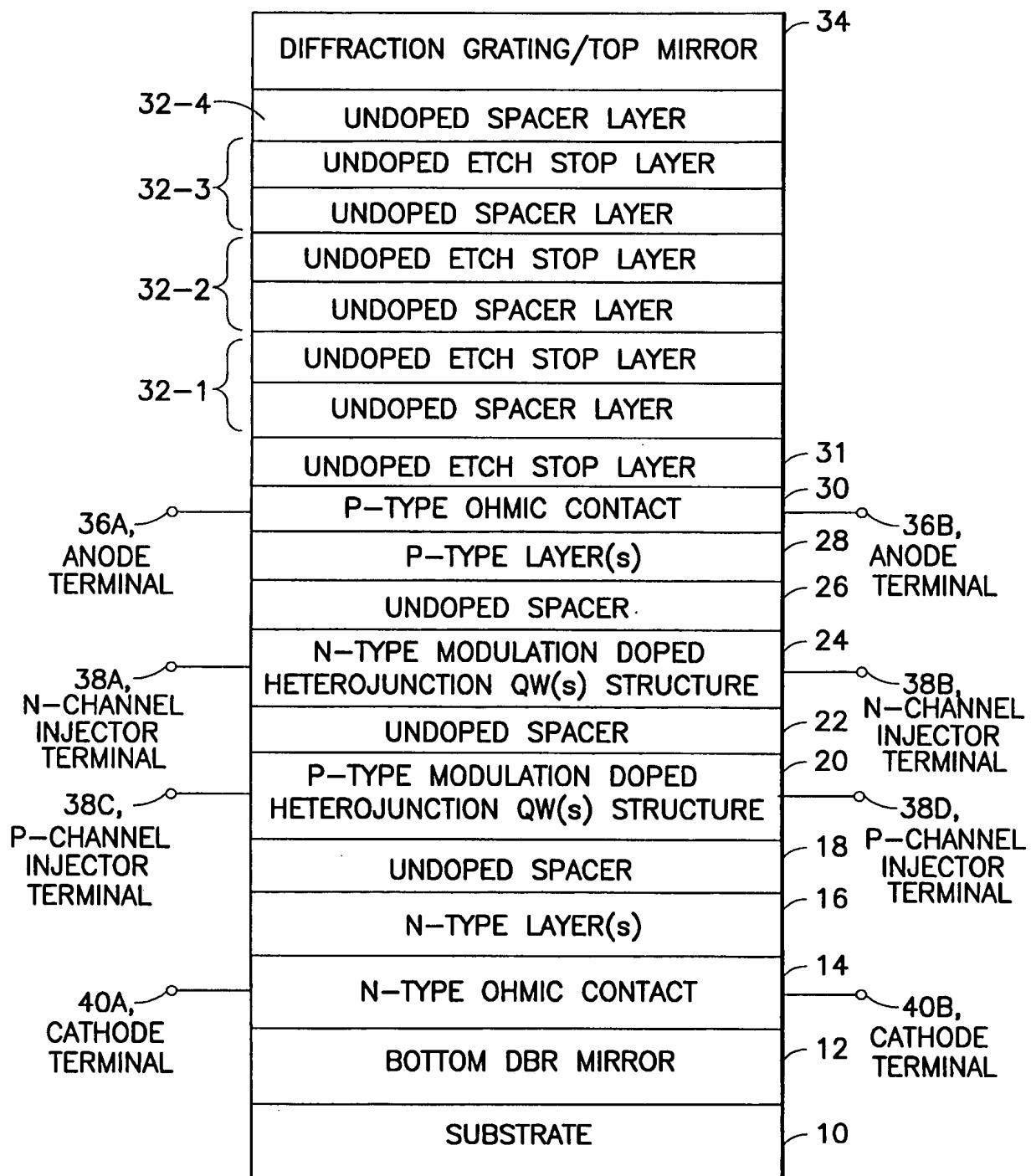
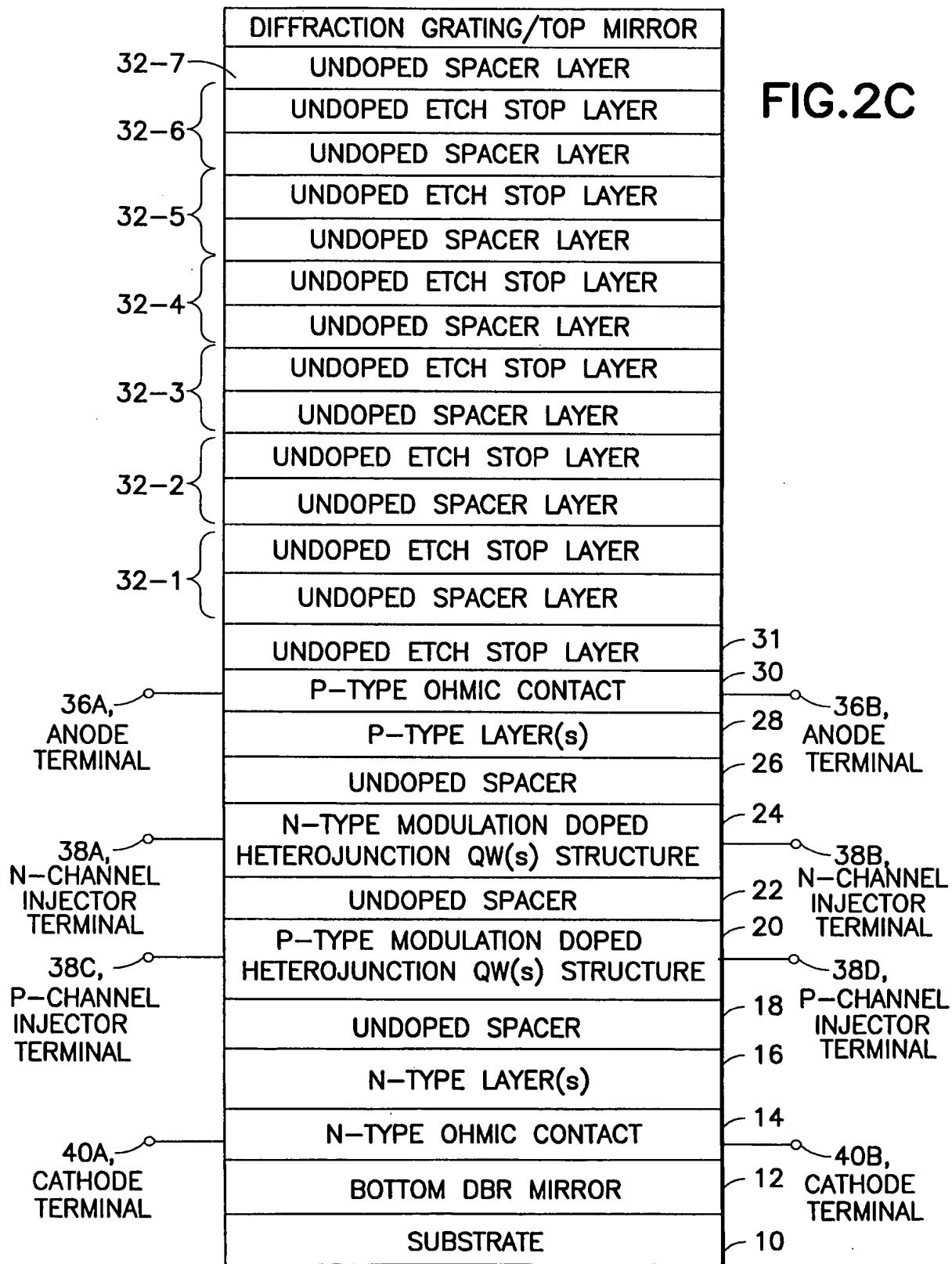


FIG.2B

FIG.2C



LAYER MATERIAL	LAYER DOPING TYPE	TYPICAL DOPING CONCENTRATION (atoms/cm <sup>3</sup> )	TYPICAL LAYER THICKNESS(Å)	LAYER #
32 { AlAs } <sup>x7</sup> —	und	und	40–100	183b
	und	und	8.75	183a
31 { AlAs	und	und	40–100	182
InGaAs	P+	1E20	25	165b
30 { GaAs	P+	1E20	75	165a
Al(0.7)Ga(0.3)As	P	1E17	700	164b
28 { Al(0.7)Ga(0.3)As	P+	1E19	10	164a
Al(.15)Ga(.85)As	P+	3.5E18	25	163d
26 { Al(.15)Ga(.85)As	und	und	200–300	163c
Al(.15)Ga(.85)As	N+	3.5E18	80	163b
24 { GaAs	und	und	20–30	163a
In(.20)Ga(.80)AsN } <sup>x3</sup>	und	und	15	162
22 { GaAs	und	und	60	161
GaAs	und	und	100	160b
20 { Al(.15)Ga(.85)As	und	und	100–250	160a
GaAs } <sup>x3</sup>	und	und	5000	159
18 { In(.20)Ga(.80)AsN }	und	und	100	158
In(.20)Ga(.80)AsN }	und	und	60	157
16 { GaAs	und	und	15	156
Al(.15)Ga(.85)As	und	und	30	155d
14 { Al(.15)Ga(.85)As	P+	3.5E18	80	155c
Al(.15)Ga(.85)As	und	und	300	155b
12 { Al(.15)Ga(.85)As	N+	3.5E18	80	155a
Al(0.7)Ga(0.3)As	N	1E17	700	154
10 { GaAs	N+	3.5E18	2200	153
AlAs } <sup>x7</sup> —	und	und	1701	151
12 { GaAs }	und	und	696	152
AlAs }	und	und	1701	151
10 { GaAs SUBSTRATE		SI		149

FIG.3

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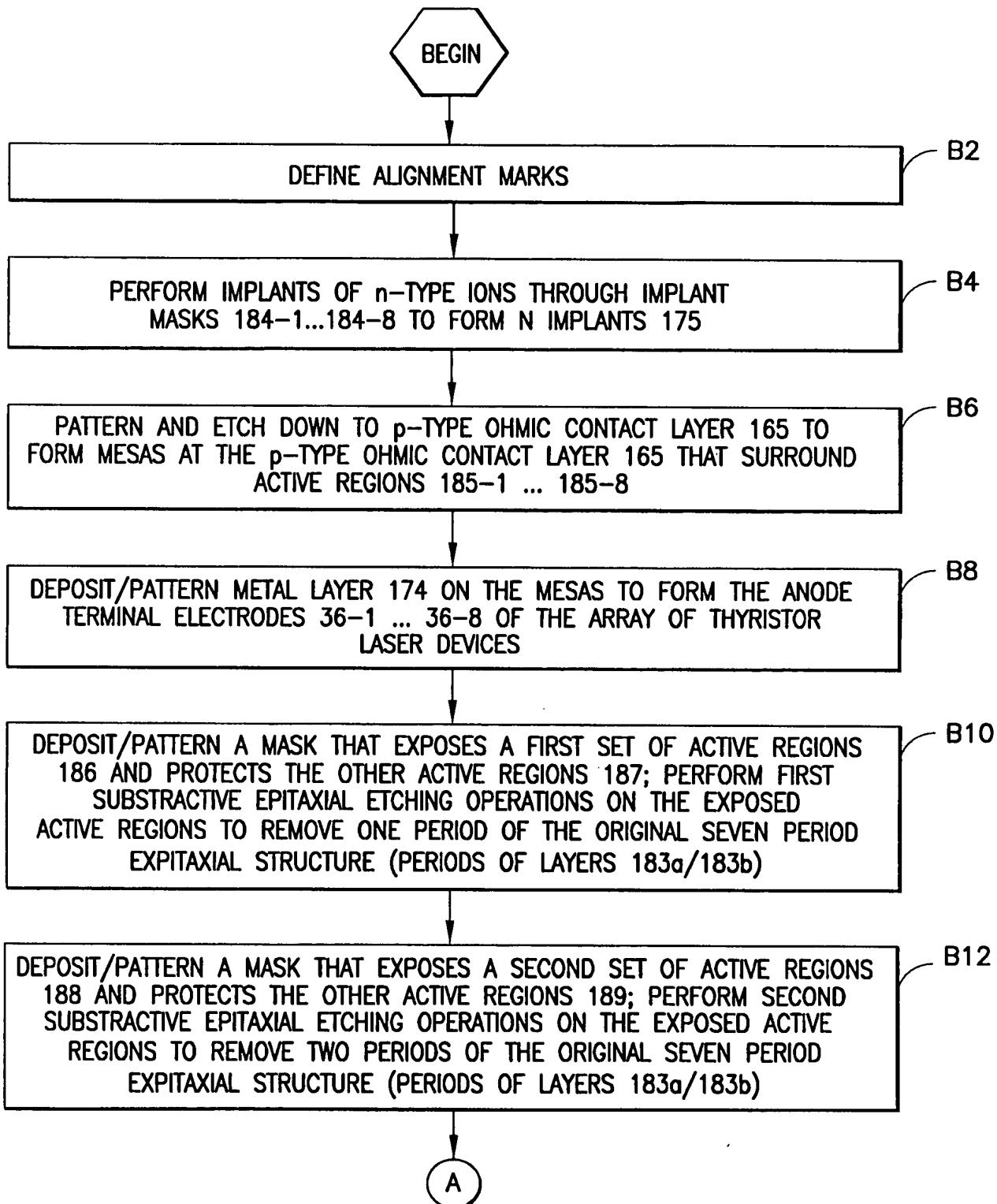


FIG.4A

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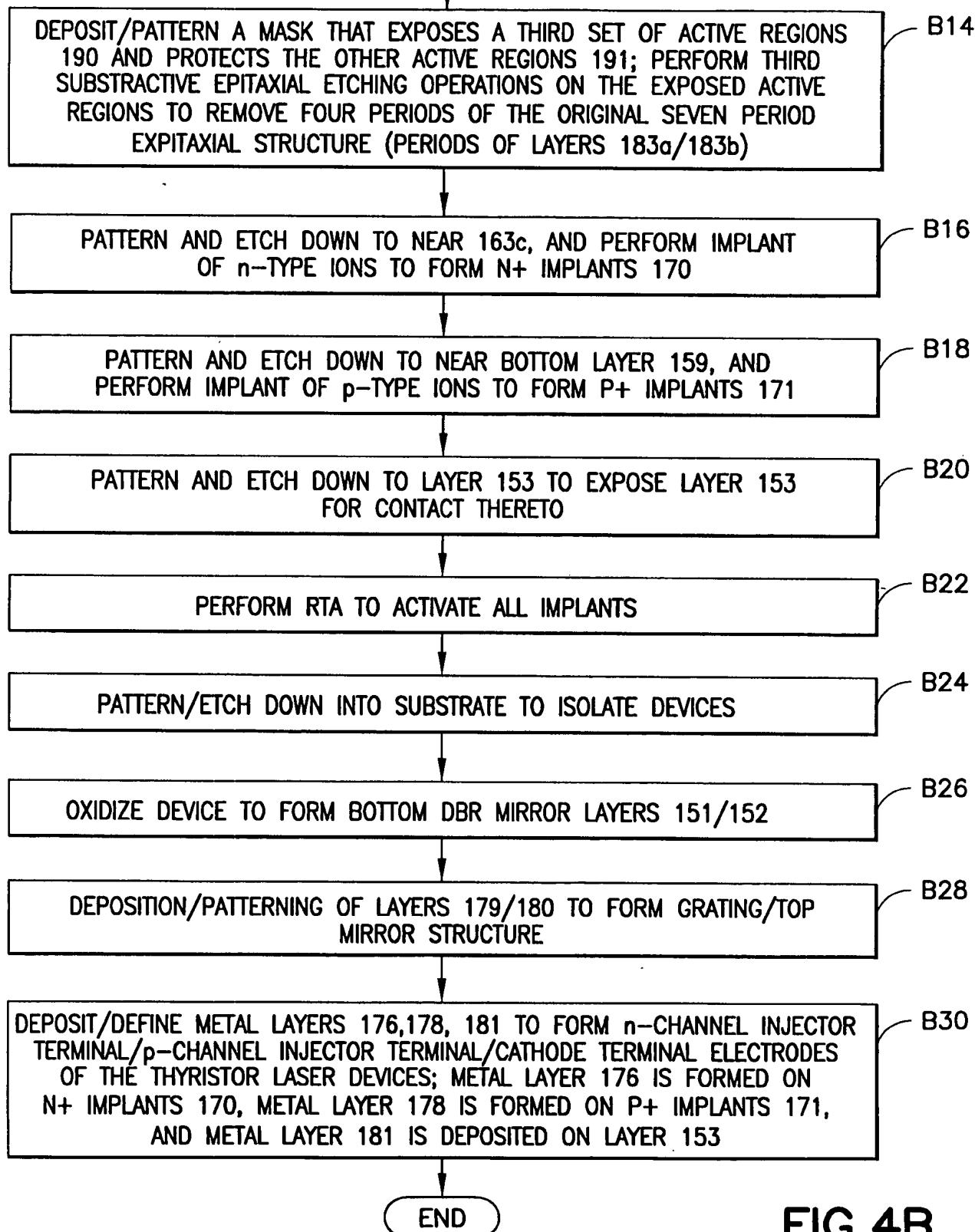


FIG.4B

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FIG.5A

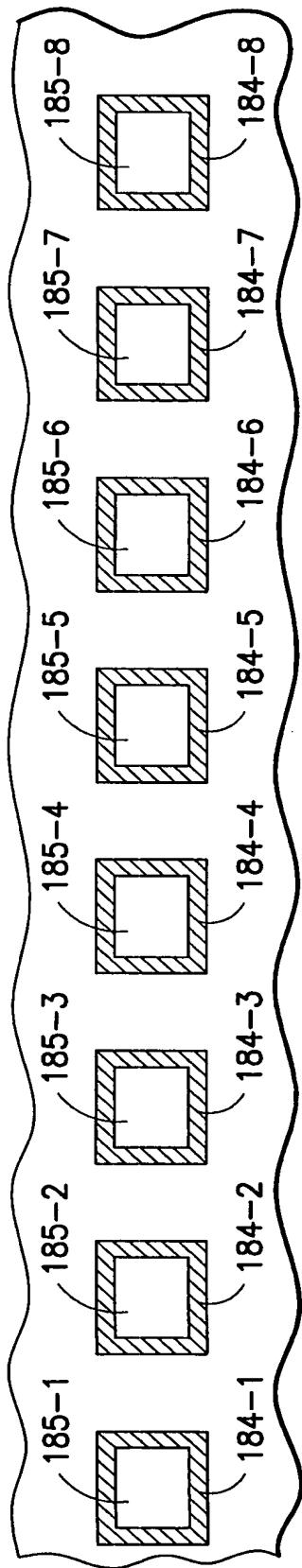
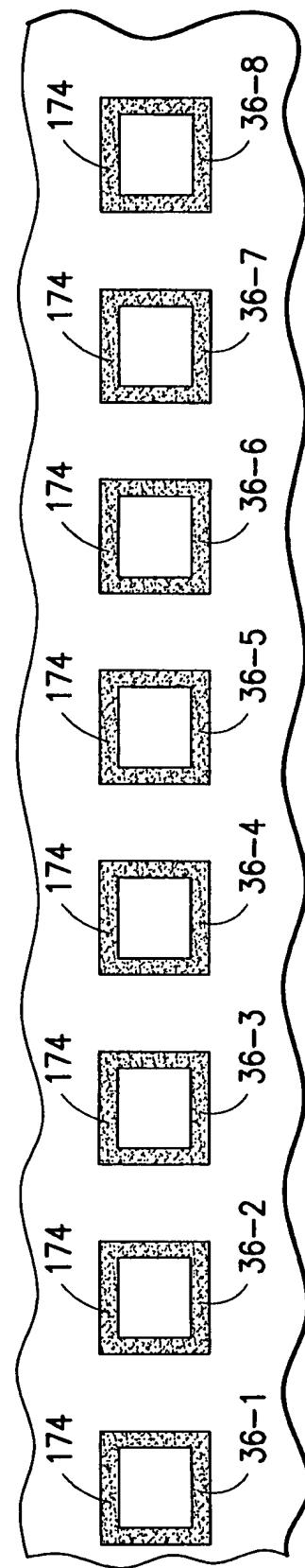
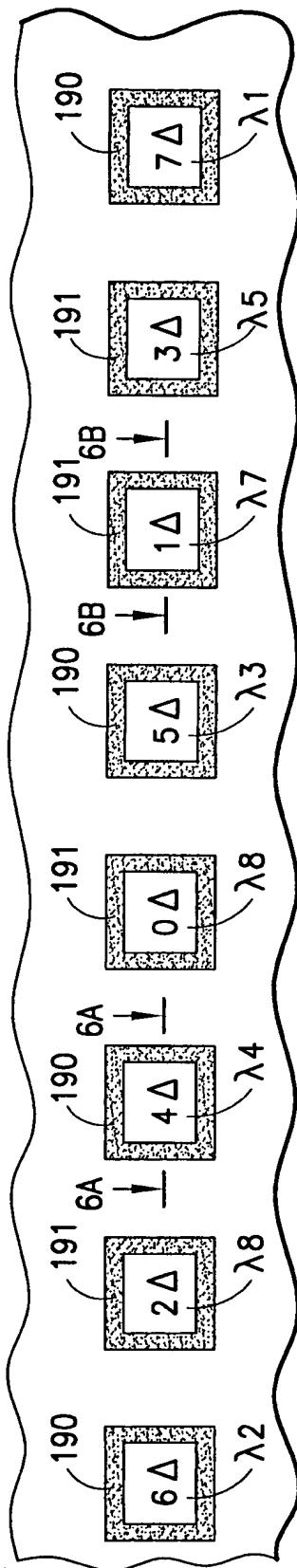
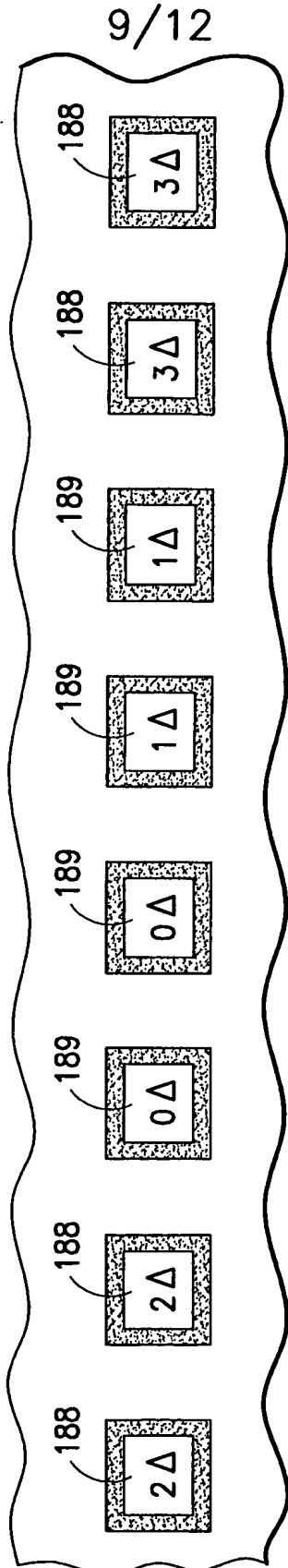
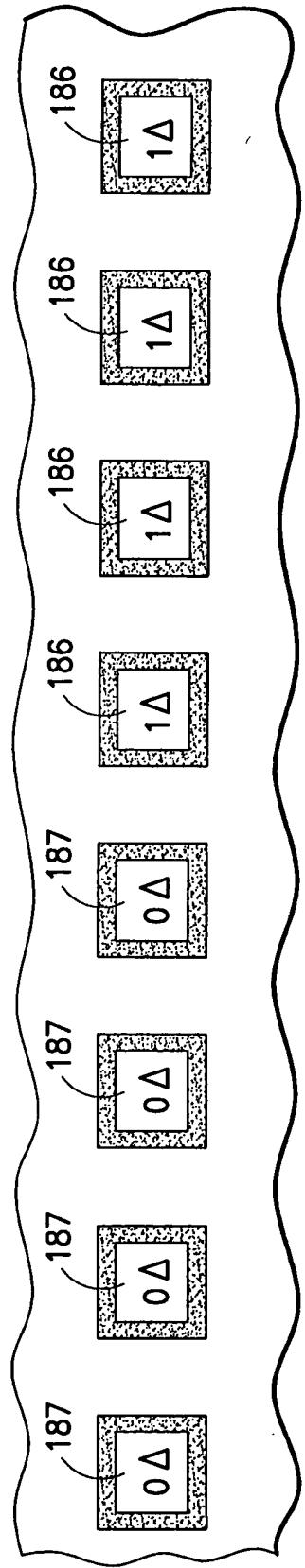
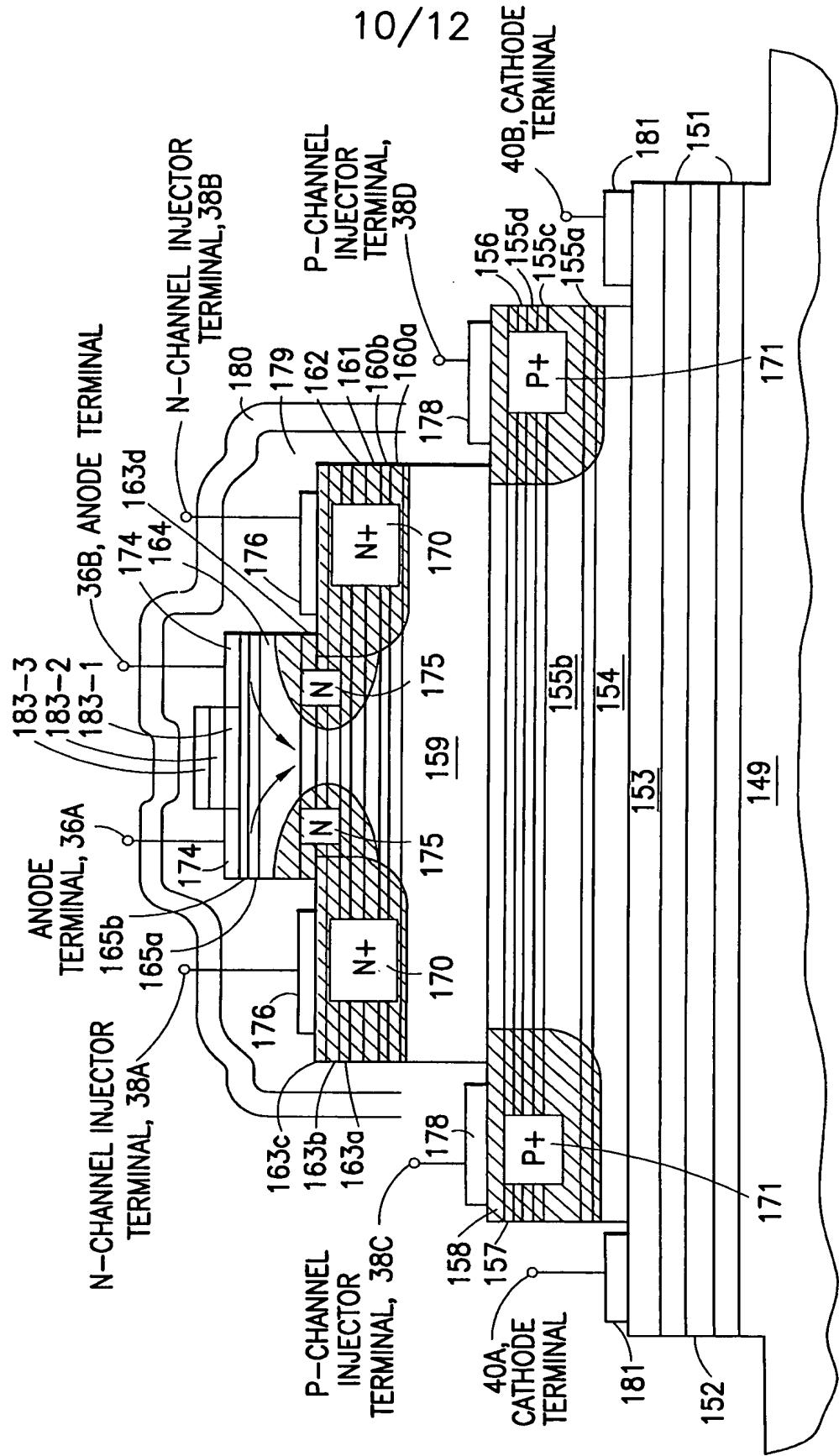


FIG.5B







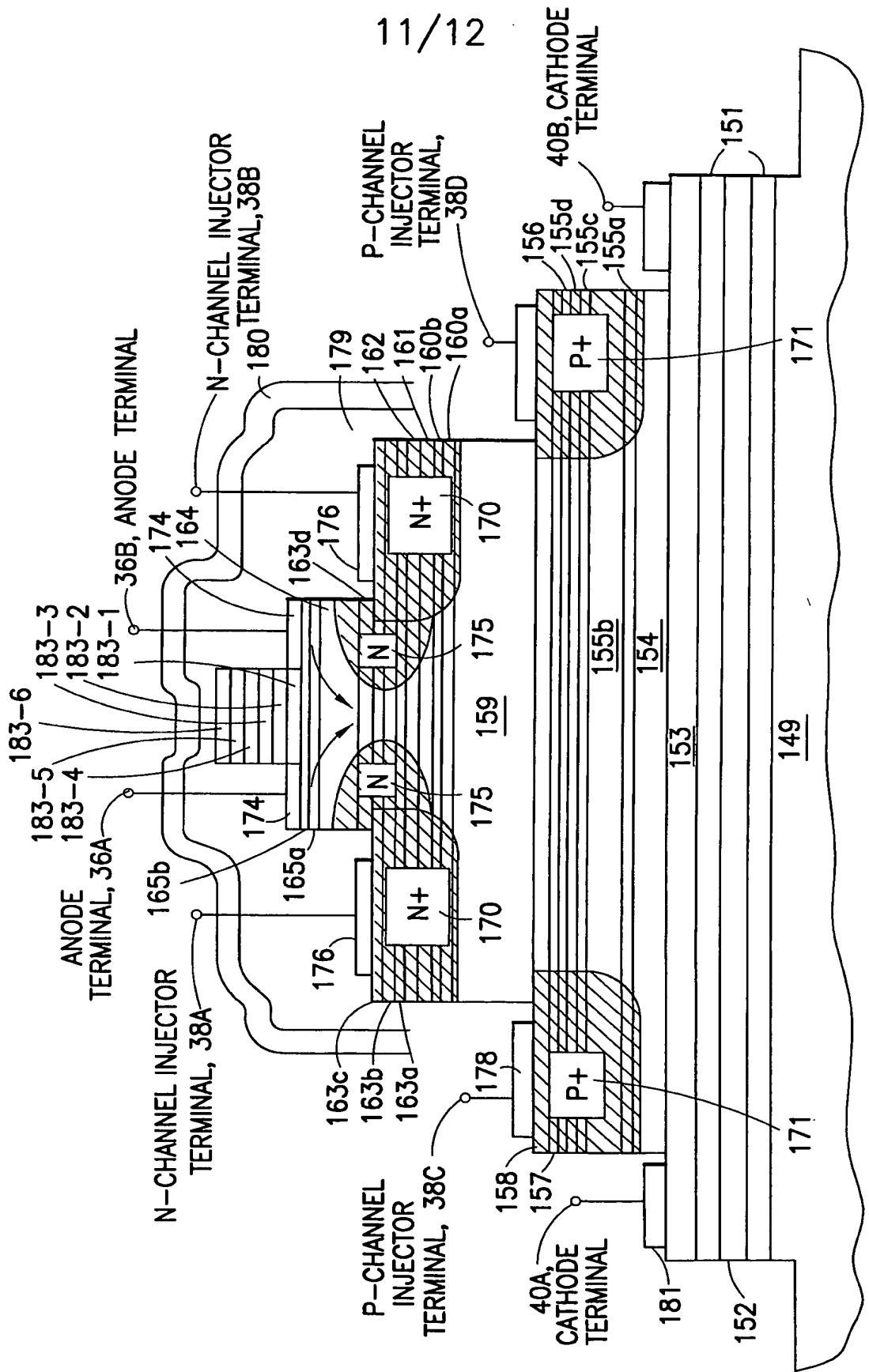


FIG. 6B

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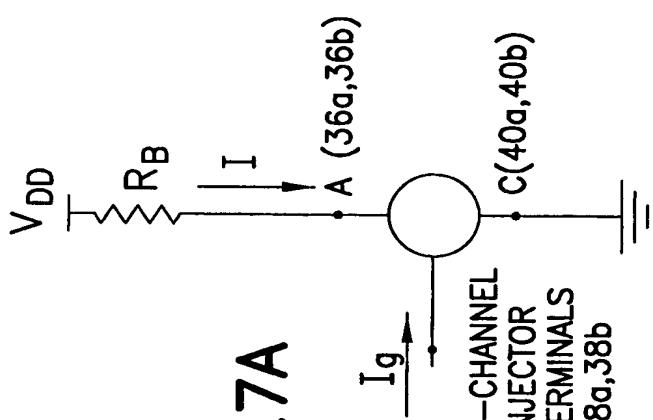


FIG. 7A

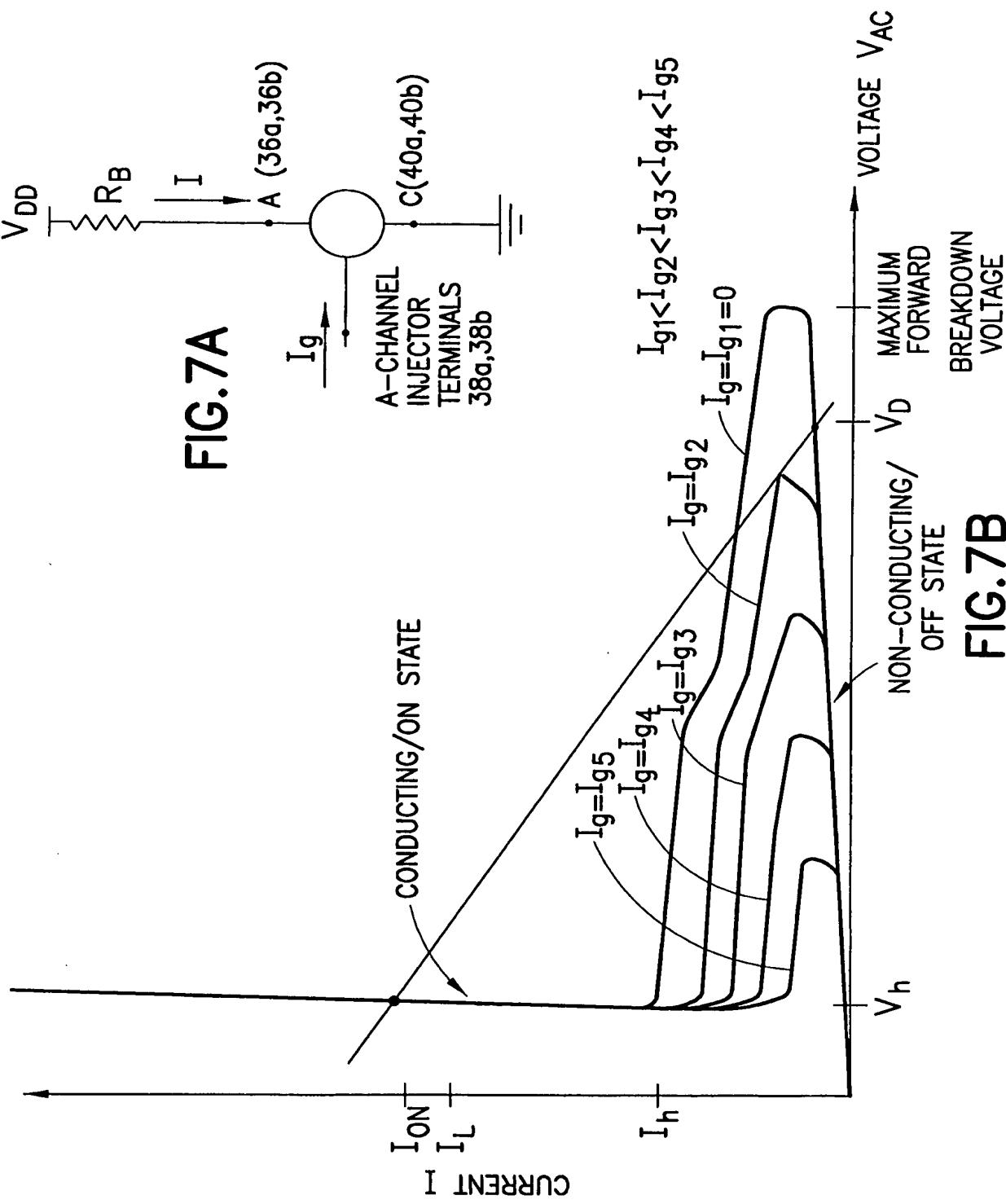


FIG. 7B